

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5859

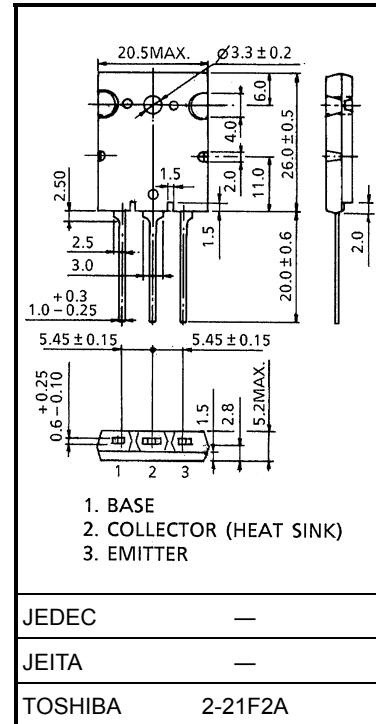
HORIZONTAL DEFLECTION OUTPUT FOR
HDTV, DIGITAL TV, PROJECTION TV

Unit: mm

- High Voltage : $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (max)}$
- High Speed : $t_f(2) = 0.1\text{ }\mu\text{s (Typ.)}$

MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	1700	V
Collector-Emitter Voltage	V_{CEO}	750	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	A
	Pulse	I_{CP}	
Base Current	I_B	11.5	A
Collector Power Dissipation	P_C	210	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight: 9.75 g (typ.)

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Min	Typ.	Max	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 1700\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	μA
Collector - Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 10\text{ mA}, I_B = 0$	750	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	20	—	55	—
	$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 8\text{ A}$	10	—	22	
	$h_{FE(3)}$	$V_{CE} = 5\text{ V}, I_C = 18\text{ A}$	4.5	—	8	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 18\text{ A}, I_B = 4.5\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 18\text{ A}, I_B = 4.5\text{ A}$	—	1.0	1.5	V
Transition Frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	320	—	pF
Switching Time	Storage Time	$I_{CP} = 8\text{ A}, I_{B1}(\text{end}) = 1\text{ A}$ $f_H = 32\text{ kHz}$	—	4	—	μs
	Fall Time		—	0.15	—	
	Storage Time	$I_{CP} = 7.5\text{ A}, I_{B1}(\text{end}) = 1\text{ A}$ $f_H = 100\text{ kHz}$	—	1.8	—	μs
	Fall Time		—	0.1	—	

